

Model for Triggered Vacuum Switches

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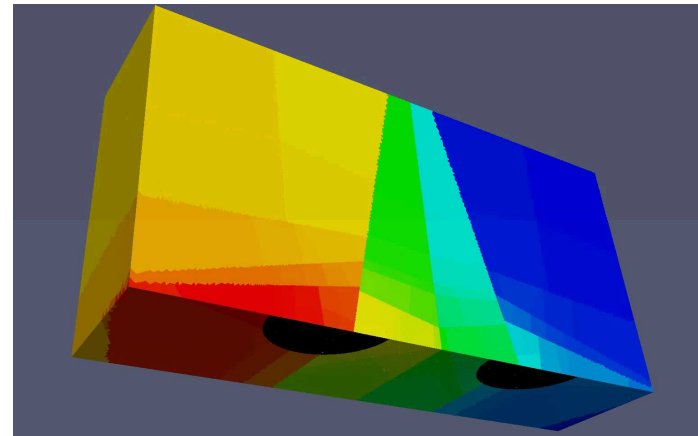
Introduction

- Triggered vacuum spark gaps (TVSGs) are useful as high voltage, high current switches
 - Fast, low variance switching time
 - Variable operating voltage
 - Limited shot life

- General TVSG operation
 - Electrodes separated by vacuum gap held at constant voltage drop
 - Trigger pulse heats a film & supplies material to the gap via vaporization
 - Vacuum → Low pressure
 - The low pressure gap breaks down due to the voltage drop

- We desire a predictive model that captures the variance in switching time and operating current from shot to shot

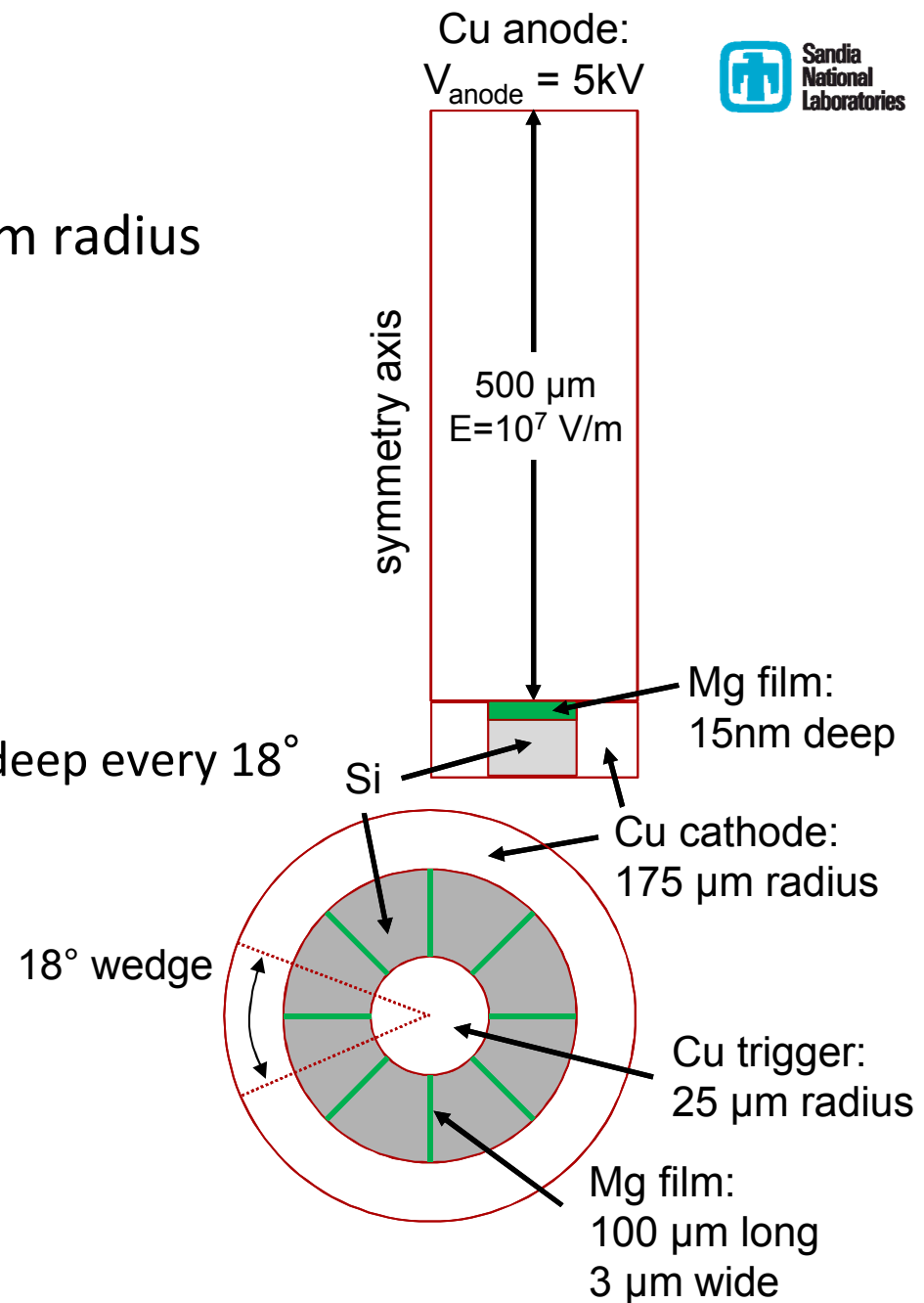
- **Electrostatic PIC + DSMC**
 - 1, 2, or 3D unstructured FEM (CAD-compatible)
 - Accounts for relative permittivity of materials
 - Can include time-varying magnetic field
- **Massively parallel (scales up to ~50K procs)**
 - Dynamic load balancing
- **Surface physics models:**
 - Fowler-Nordheim, thermionic, and Murphy-Good e^- emission models
 - Sputtering, surface charging, auger-neutralization, SEE, photoemission, sublimation
 - Can use time-varying pre-computed flux files (e.g., from data)
- **Direct Simulation Monte Carlo Collision physics:**
 - Simulate all species as simulation particles with variable particle weights
 - Can simulate evolution of neutral gas densities (important at low pressures)
 - Elastic, charge exchange, chemistry (dissociation, exchange, etc.), excited states (w/ radiative decay & self-absorption), ionization, Coulomb collisions (Nanbu model)



Automatic Domain Decomposition

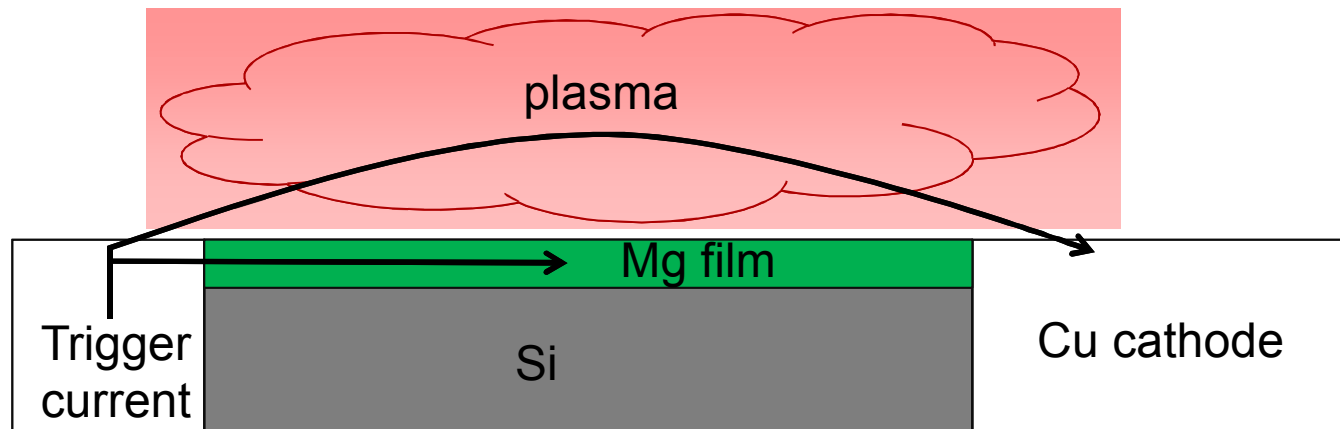
TVSG: Geometry

- 500 μm vacuum gap with 175 μm radius
- Inner ring
 - Cu trigger with 25 μm radius
- Middle ring
 - Si with 125 μm outer radius
 - Mg “wire”: 3 μm wide \times 15 nm deep every 18°
- Outer ring
 - Cu cathode
- If 100% of the Mg wires vaporize then $n_{\text{Mg}} \approx 10^{23} \text{ m}^{-3}$



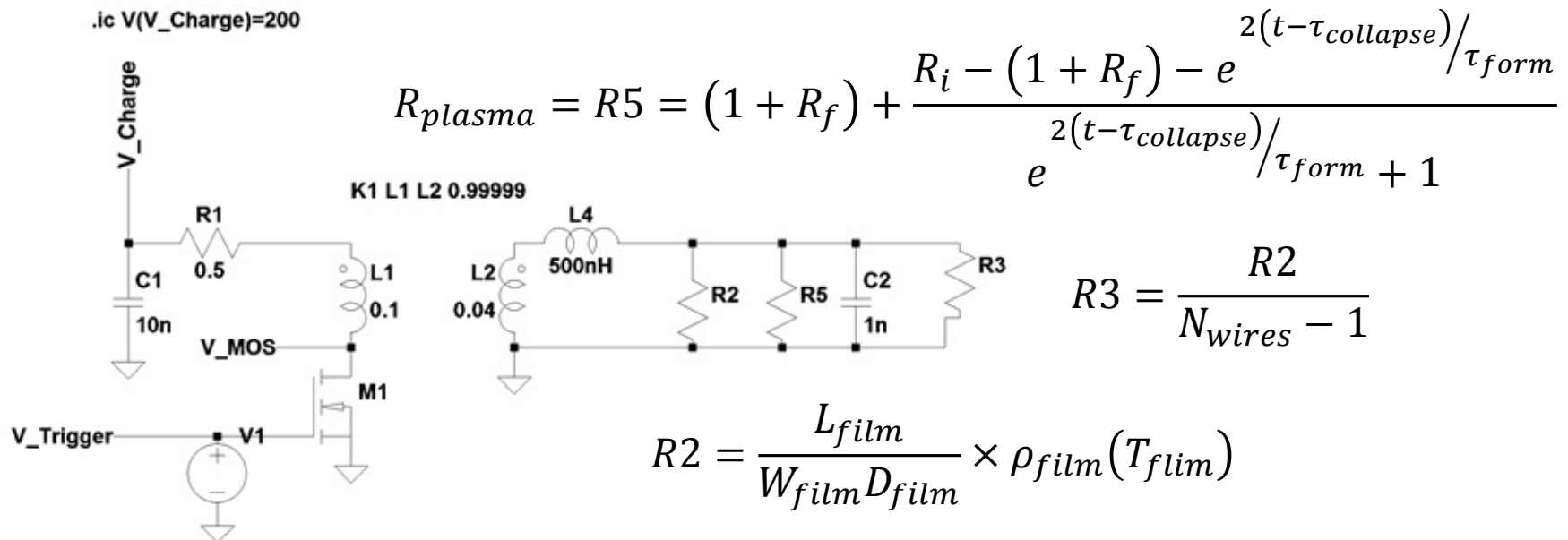
External Trigger Circuit

- Increasing the trigger input voltage leads to joule heating in the film and material emission
- Plasma forms over the film and provides an alternative conduction path that steals current from the film
- Film and plasma act like two varying resistors in parallel



External Trigger Circuit: Spice Model

- Trigger circuit driven by a capacitor with 200V initial charge
- Plasma resistance varies in time ($R_i = 2000\Omega$; $R_f = 0.1\Omega$)
 - τ_{form} = Plasma formation time = 20ns
 - τ_{collapse} = Trigger-cathode breakdown delay time = 200ns
- Extract the current vs. time through the R2 resistor
 - R3 resistor accounts for the other parallel Mg film “wire spokes”

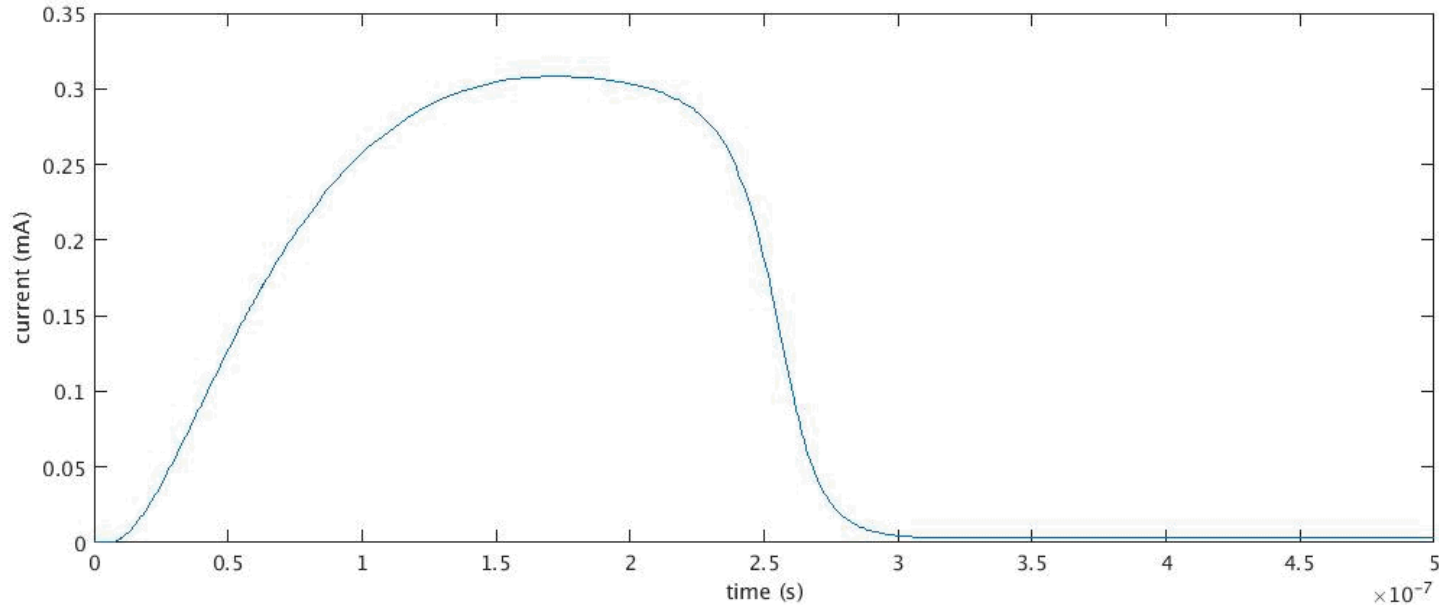


External Trigger Circuit: Film Current

- Mg resistivity varies by >4x from 300K to $T > 1200\text{K}$ during triggering:

$$\rho_{Mg}(T) \cong 0.143T + 2$$

- Until we couple the external circuit solve to the PIC simulation we must use a constant value for Mg resistivity. Use $\rho_{Mg}(1000\text{K}) = 145 \text{ n}\Omega\cdot\text{m}$
 - $R2 = 322 \text{ }\Omega$
- Film depth change negligible: triggering uses $\sim 1\%$ of total film mass

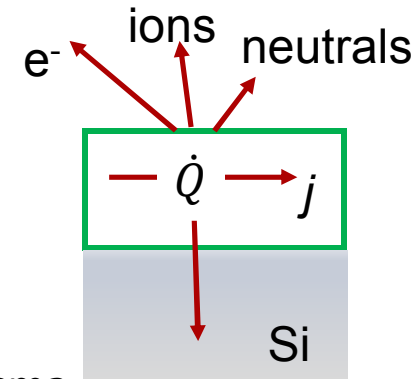


TVSG: 1D Thermal Model

- Solve 1D heat conduction equation in the film (assume $\kappa = \text{const}$)

- Film is 3 μm wide vs. 15 nm deep

$$C_p \rho \frac{\partial T}{\partial t} - \kappa \frac{\partial^2 T}{\partial z^2} = \frac{j(t)^2}{\sigma_{\text{film}}(t)} \quad T(t, z = 0) = 300$$
$$\kappa \frac{\partial T}{\partial z} \Big|_{z=h} = q_i + q_n + q_e + q_{\text{rad}}$$



- q_{rad} :

- Small compared to other terms \rightarrow neglect from surface and plasma

- q_e :

- Murphy-Good e^- emission (Benilov and Benilova, *J. Appl. Phys.* **114**, 2013)
- Inversion temperature for Nottingham effect (emissive heating) < 30 K
- Heating due to return e^- current assumed negligible ($T_e < 100$ eV)

- q_n & q_i

- Model for *initiation* (breakdown time), so ion & neutral heating of film neglected
- Assume evaporative cooling via Hertz-Knudsen vaporization to compute flux
- Specifics depend on sublimation vs. explosive emission models

- Use Murphy-Good emission (with $\beta=25$):

$$j_e(E, T, \zeta) = e \int_{-W_a}^{\infty} D(E, W) N(T, \zeta, W) dW$$

- Use computationally efficient approach of Benilov and Benilova, *J. Appl. Phys.* **114** (2013) to solve for current density:

$$j_e(T_{film}, E_w, \varphi) = (I_1 + gI_2) A_{em} T_{film}^2$$

- I_1 and I_2 are numerically solved integrals; $g = \frac{1}{kT_w} \sqrt{\frac{e^3 E_w}{4\pi\epsilon_0}}$

- We assume the electrons come off at the film wall temperature:

$$q_e = -\frac{j_e}{e} (2kT_{film} + \phi_s)$$

- Cu trigger and cathode emit using Fowler-Nordheim

- Compute fluxes from Hertz-Knudsen vaporization with Antoine vapor pressure for Mg ($A=13.495$, $B=-7813$, $C=-0.8253$):

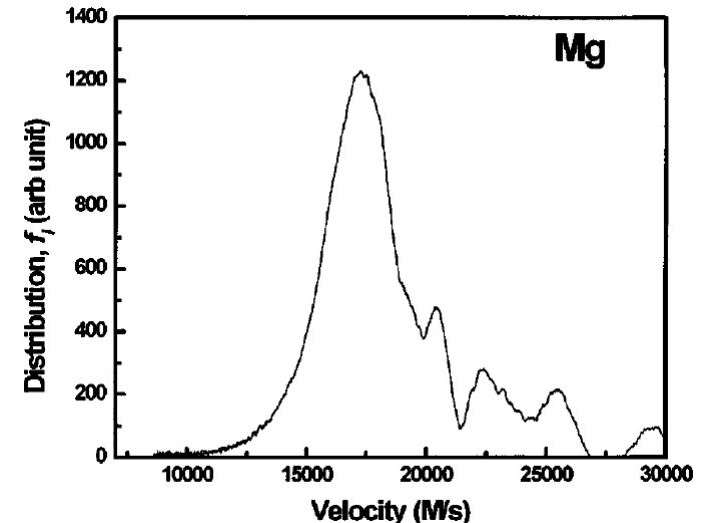
$$\Gamma = \frac{P_{vap}}{\sqrt{2\pi mkT_{film}}}, \quad \log(P_{vap}) = A + \frac{B}{T_{film}} + C \log(T_{film})$$

- Questionable validity for $T_{film} > T_{boiling}$. However, energy deposited into the film via joule heating either heats the film (and increases material fluxes) or is conducted away (relatively small)
 - If $T_{film} > T_{boiling}$ and the physical flux rate should be larger than Hertz-Knudsen rate then the film temperature will increase until:

$$\Gamma_{real}(T_{film,real}) \approx \Gamma_{H-K}(T_{film,model})$$

- Because this requires heating the film further we still get the transient flux wrong as there is a lag (esp. near $T_{film}(t) \sim T_{boiling}$?)

- 1D thermal model finds that the temperature at the film surface is less than the bulk film temperature
 - Possibility of phase transition to vapor under the surface in the bulk that leads to explosive emission once the pressure is high enough
- $V_{\text{Mg}^+} \sim 20 \text{ km/s}$ ($\sim 50 \text{ eV}$) from prior vacuum arc data [1]
- Are the ions formed via ionization of neutrals and then expand at the ion sound speed or during an explosive process in the film?
 - We will investigate several options with four models



[1] Byon & Anders, *JAP* **93**, 1899 (2003)

- We still need to know the energy carried away by each neutral/ion. Four models are examined:

- Sublimation (thermal bulk velocity away from film):

$$q_{neutral} = -\Gamma(2kT_{film} + E_{coh})$$

- Fast Sublimation ($\sim 20\text{km/s}$ bulk velocity):

$$q_{neutral} = -\Gamma(2kT_{film} + E_{coh} + 0.5mv_{bulk}^2)$$

- Explosive Neutrals: ($\sim 20\text{km/s}$ bulk velocity when $T_{film} > T_{boiling}$):

$$q_{neutral} = \begin{cases} -\Gamma(2kT_{film} + E_{coh}), & T_{film} < T_{boiling} \\ -\Gamma(2kT_{film} + E_{coh} + 0.5mv_{bulk}^2), & T_{film} > T_{boiling} \end{cases}$$

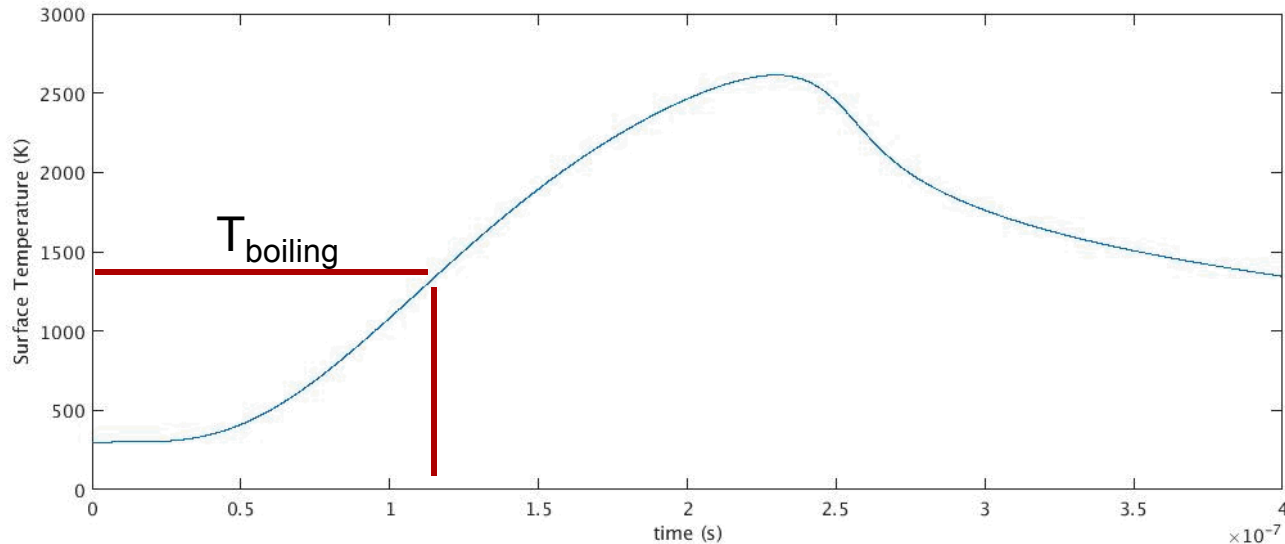
- Explosive Ions (ion emission when $T_w > T_{boiling}$):

$$q_{neutral} = -\Gamma(2kT_{film} + E_{coh}), \quad T_{film} < T_{boiling}$$

$$q_{ion} = -\Gamma(2kT_{film} + E_{iz} - \phi_S + E_{coh}), \quad T_{film} > T_{boiling}$$

TVSG: Surface Temperature

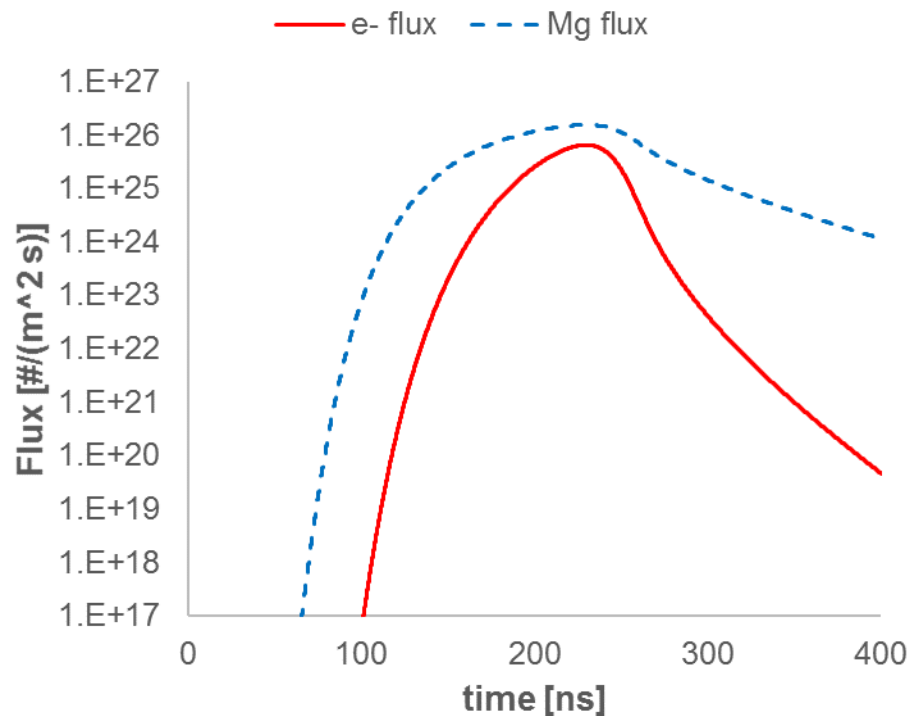
- Slight variations in surface temperature depending on neutral emission model
- Surface temperature $> T_{\text{boiling}}$ after $\sim 115\text{ns}$
 - If T_{film} held to less than T_{boiling} (by adjusting the trigger circuit to obtain lower film current densities):
 - Not enough surface material/ e^- are supplied \rightarrow Gap does not break



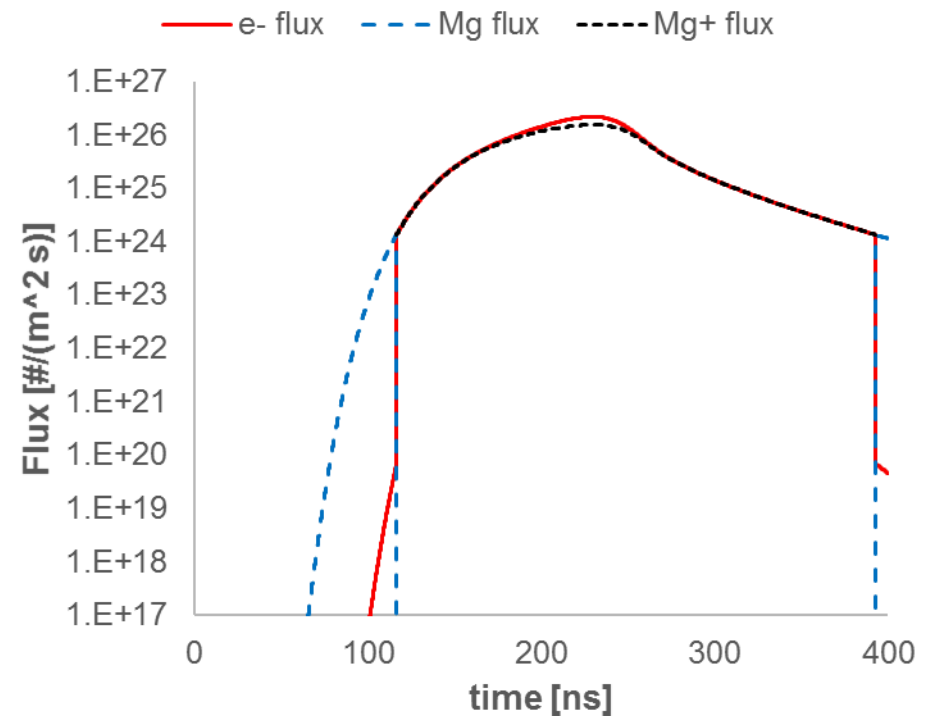
TVSG: Emission Fluxes

- Slight variation on total material emission based on emission model
- Total emitted material would fill gap to $n \sim 10^{21} \text{ \#}/\text{m}^3$
 - Paschen breakdown \rightarrow no breakdown; would need $\sim 10\times$ more material
- Very little material emission until $\sim 75\text{ns}$ \rightarrow shift $t_{\text{sim}} = 0$ by 75ns

Neutral Sublimation:



Explosive Ion Emission:



■ Sputtering [1]:

- Generalized equation based on impactor and target masses, impactor KE, and several fit parameters:

$$Y(E) = 0.042 \frac{Q(Z_T)\alpha^* \left(M_T/M_I\right)}{U_S} \frac{S_n(E)}{1 + \Gamma k_e \epsilon^{0.3}} \left[1 - \sqrt{\frac{E_{th}}{E}} \right]^s$$

■ Ion-induced SEE:

- Low energy limit [2]:

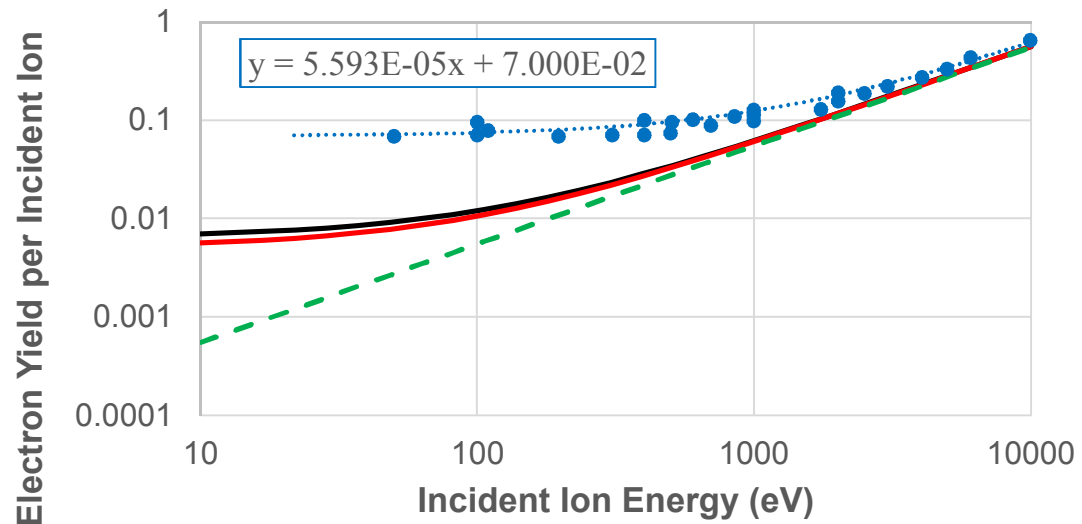
$$\gamma_{SEE} \approx 0.016(E_{IZ} - 2\phi)$$

- High energy based on [3]

- Fit Ar⁺ yield data on diff. surfaces (~const ϕ)
- Assume same high energy behavior for Cu⁺ and Mg⁺

- SEE yield is very low

● Ar⁺ on various [2] — Cu⁺ on Mg — Mg⁺ on Mg — Ion on Cu



[1] Y. Yamamura and H. Tawara, *Atomic Data and Nuclear Data Tables* **62**, 149-253, (1996).

[2] Y. Raizer, *Gas Discharge Physics* (1991)

[3] A.V. Phelps and Z. Lj. Petrović, *PSST* **8**, R21, (1999). Figure 2

TVSG: Collisions

■ $e^- + \text{Cu}$ [1]

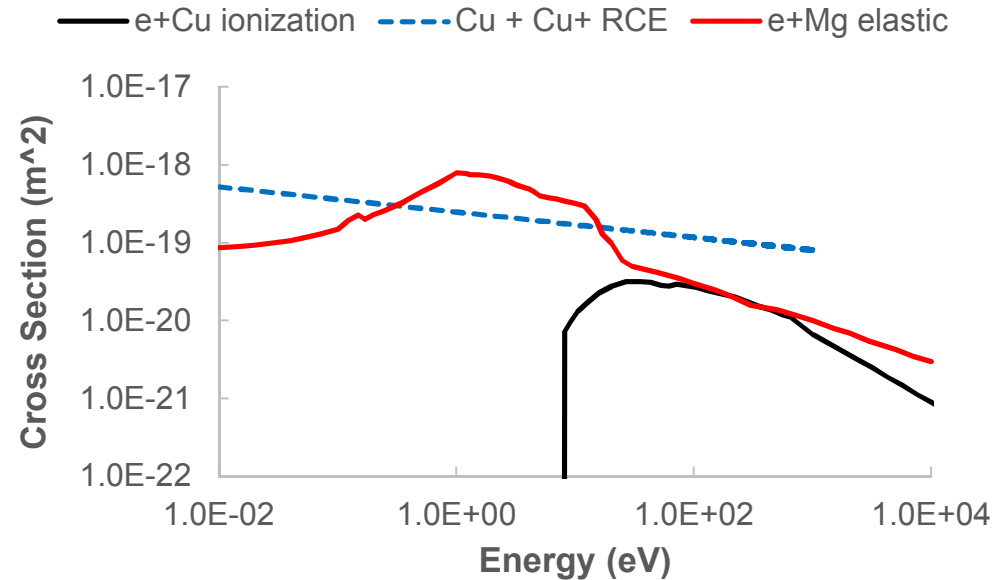
- Elastic (isotropic scattering)
- 4 excited states
- Ionization to Cu^+

■ $e^- + \text{Mg}$ [2]

- Elastic (isotropic scattering)
- 2 excited states
- Ionization to Mg^+

■ Neutral collisions

- $\text{Cu} + \text{Cu}$ elastic and $\text{Cu} + \text{Cu}^+$ resonant charge exchange [3]
- $\text{Mg} + \text{Mg}^+$ resonant charge exchange [4]
- $\text{Cu} + \text{Cu}^+$ elastic isotropic scattering, VHS [5]
- $\text{Cu} + \text{Mg}$, $\text{Mg} + \text{Mg}$, $\text{Mg} + \text{Mg}^+$ elastic isotropic scattering, VHS [5]



[1] SIGLO database, www.lxcat.net, retrieved on 9/30/2014

[2] Phelps database, www.lxcat.net, retrieved on 2/14/2017

[3] A. Aubreton and M. F. Elchinger, *J. Phys. D: Appl. Phys.* 36(15), 1798-1805 (2003).

[4] Smirnov, *Physica Scripta* **66**, 595-602 (2000).

[5] G. A. Bird, *Molecular Gas Dynamics and the Direct Simulation of Gas Flows* (1994).

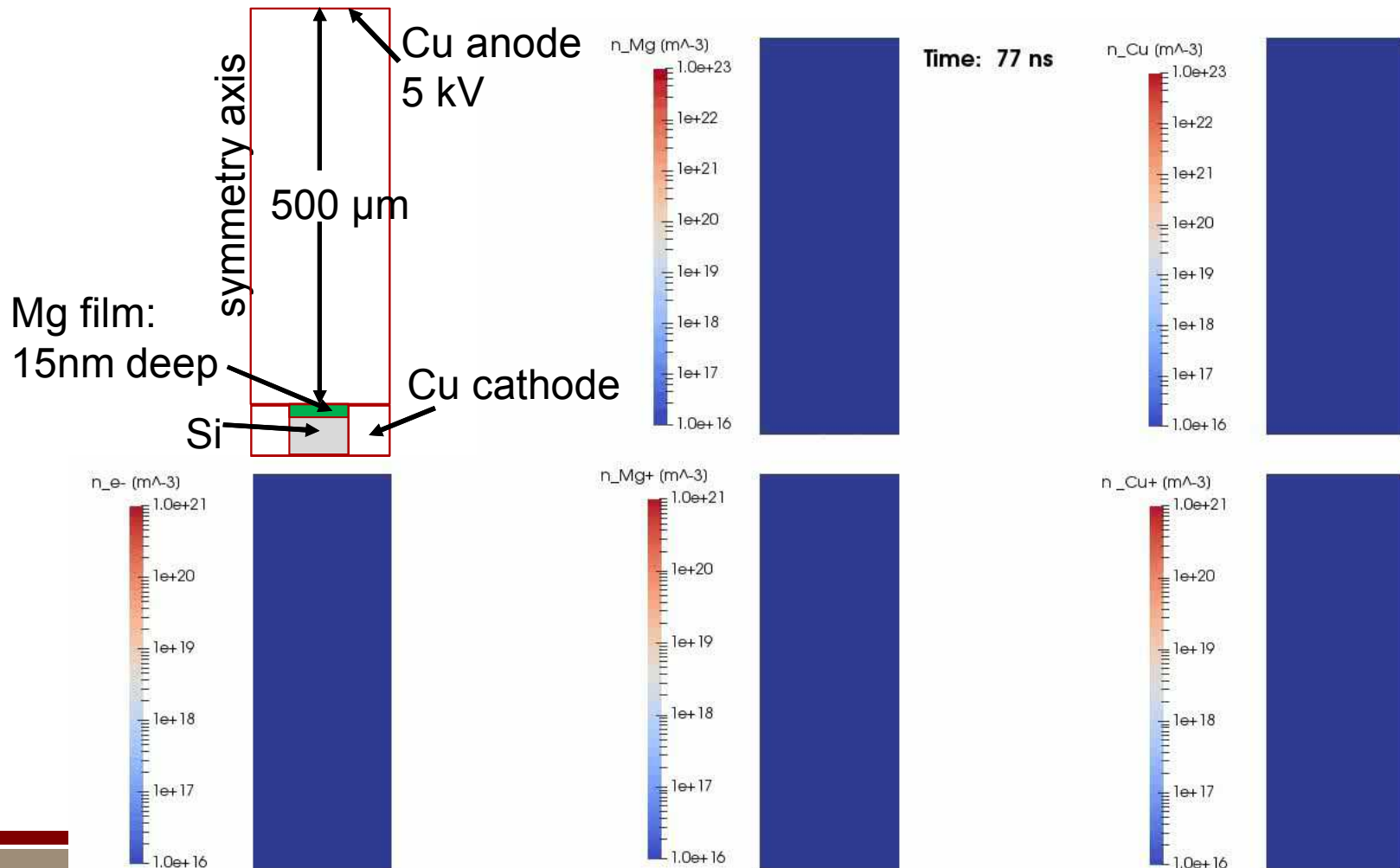
Numerical Parameters

- Δx must resolve Debye length. Assume plasma density $\leq 10^{21} \text{ \#/m}^3$ and $T_e \geq 10 \text{ eV} \rightarrow \Delta x = 2.35 \text{ \mu m}$ near the film
 - Allow for mesh to grow slightly away from the film
 - $\sim 10^6$ elements
- Δt must resolve
 - Collision rate: $\Delta t < \frac{1}{\nu_e} = 10^{-12} \text{ s}$
 - Plasma frequency: $\Delta t < \frac{1}{\omega_{pe}} = 10^{-12} \text{ s}$
 - CFL: $\Delta t < \frac{\Delta x}{v_e} \sim \frac{10^{-6}}{10^7} = 10^{-13} \text{ s}$
 - We use $\Delta t = 2 \times 10^{-13} \text{ s}$
 - Acceptable error that a small fraction of electrons will violate CFL
- Particle weights: Use particle merging to keep $\text{\#/element} \sim 100$

Each simulation took
1-2 days on 4096 cores

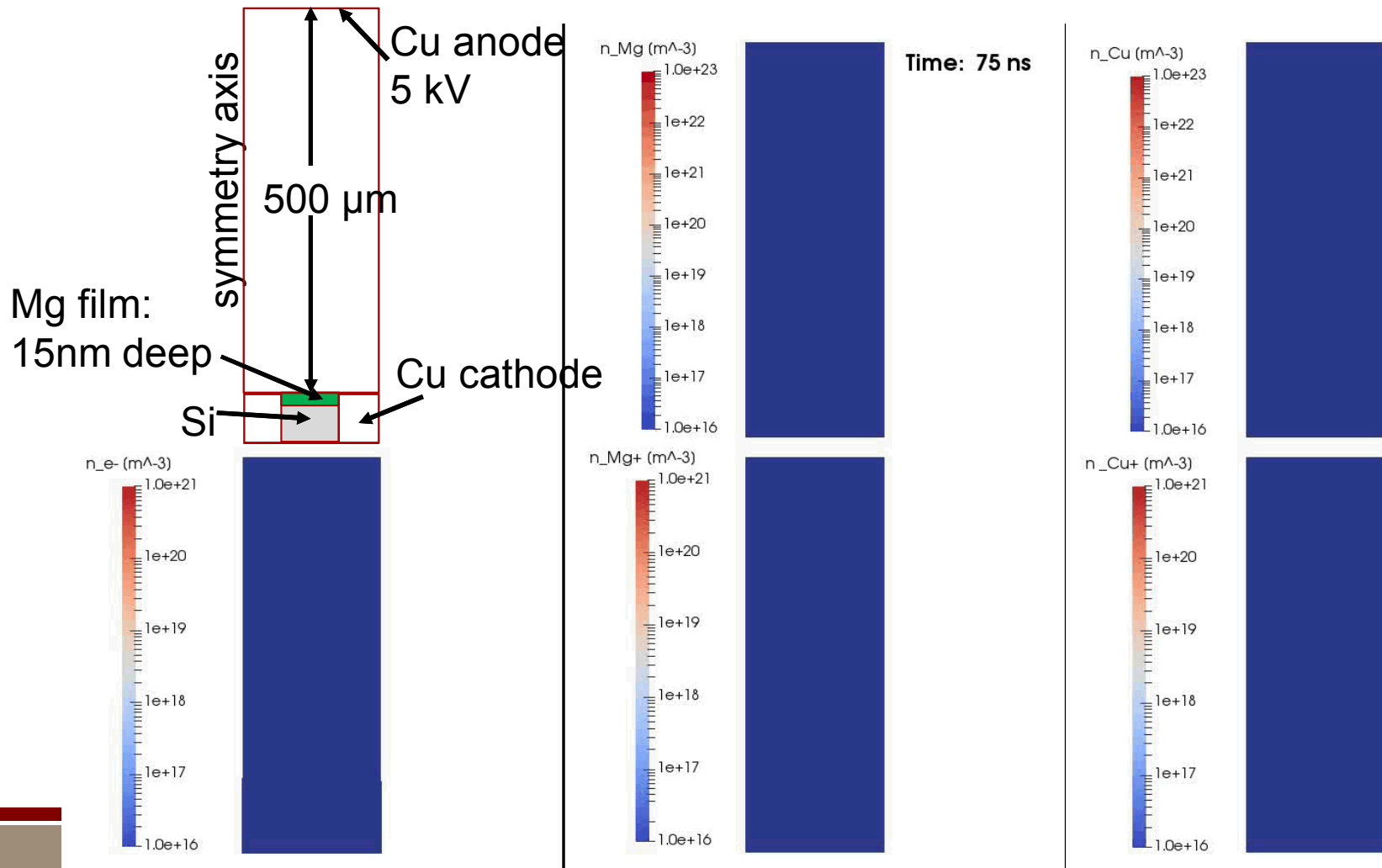
Results: Neutral Sublimation

- Does not breakdown: Sputtering does not increase neutral density enough given small ion-induced SEE
- Plasma density $\sim 10^{21}$ and $T_e \sim 5\text{eV}$: Mesh OK, but gap didn't breakdown



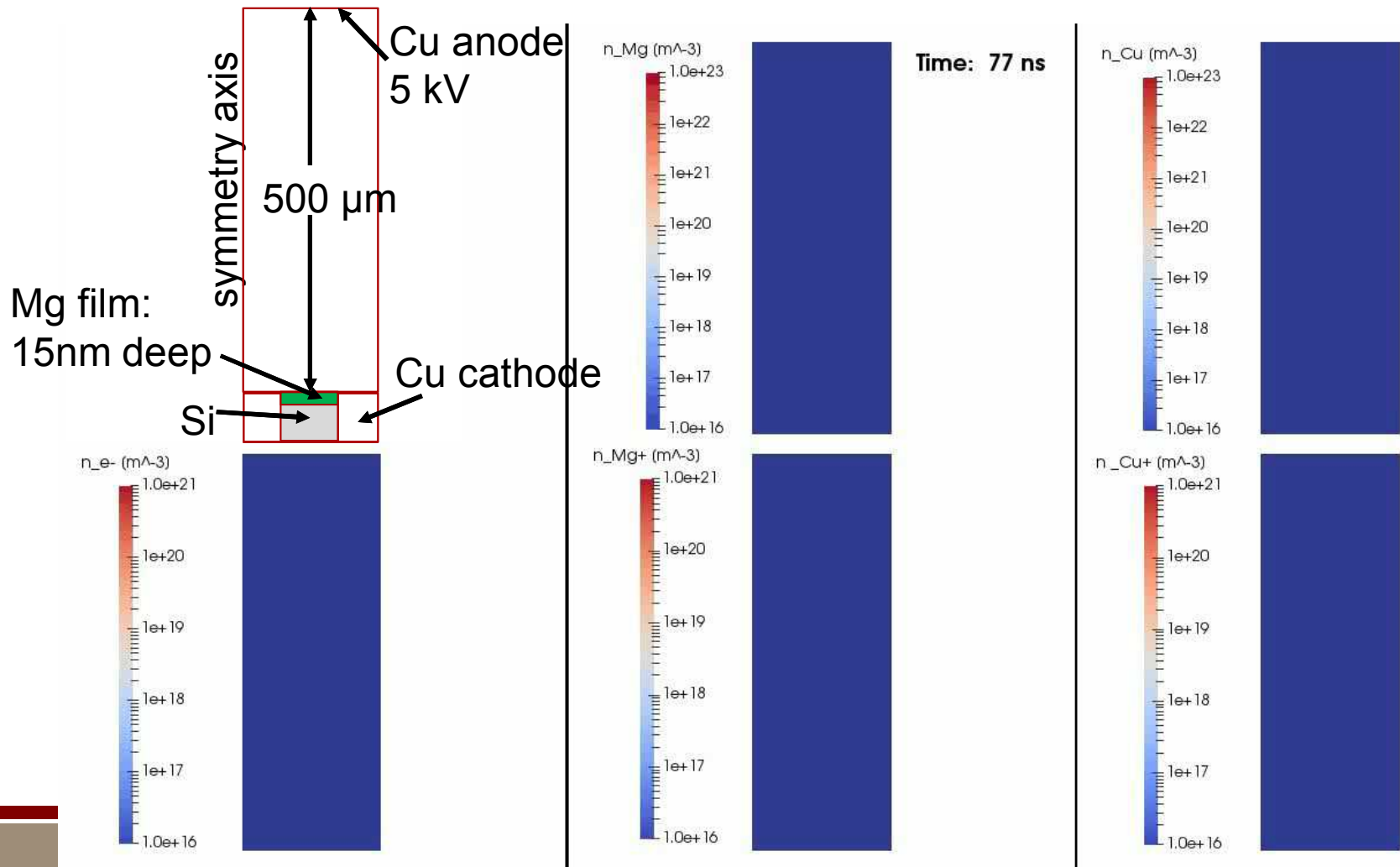
Results: Fast Neutrals

- Fast neutrals produced from cathode emission stream across gap and sputter significant anode electrode material *before* breakdown
 - If explosive emission produces ions we don't expect early-time anode sputtering



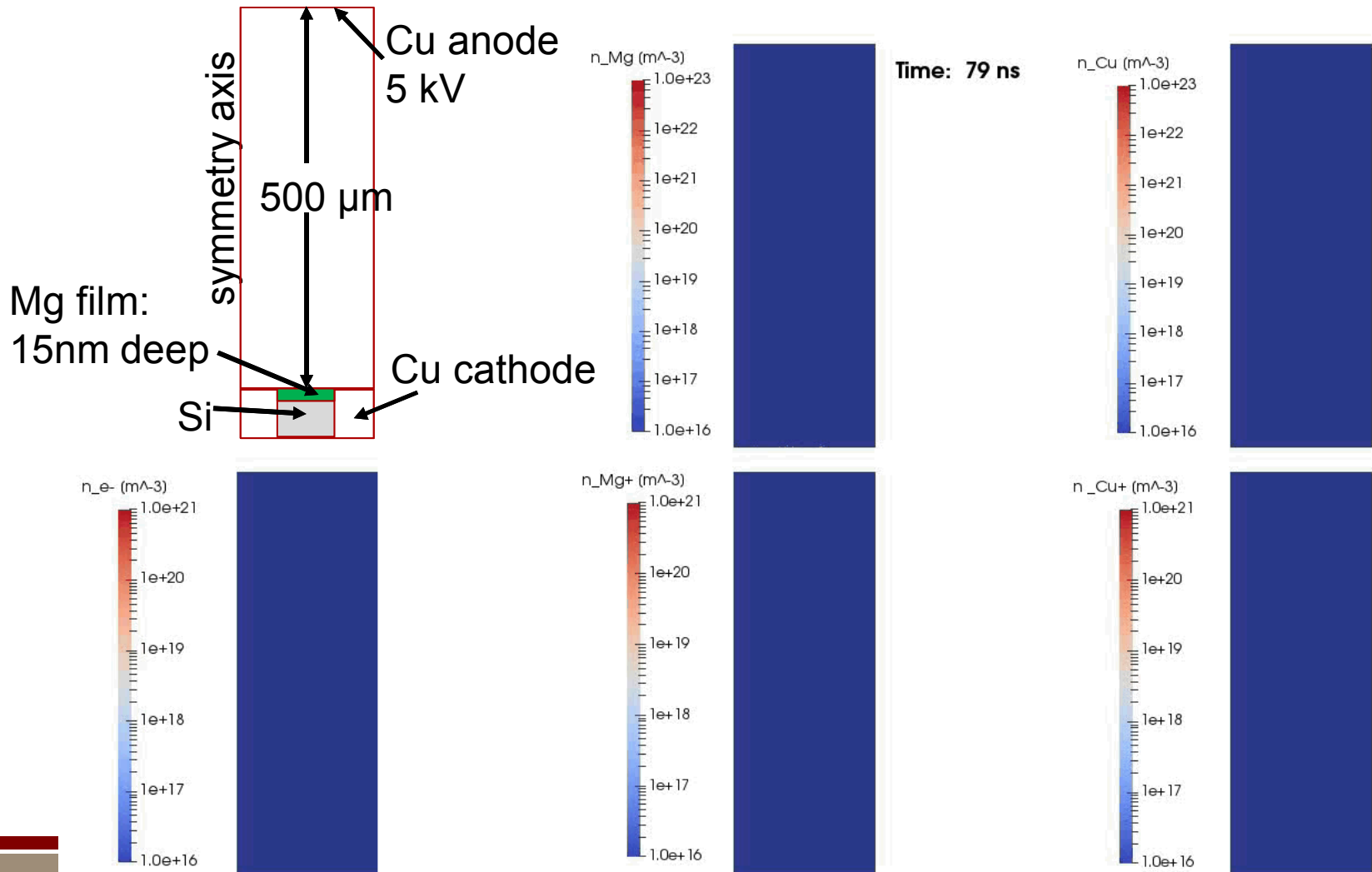
Results: Explosive Neutrals

- Still have significant anode sputtering due to fast neutral collisions as “cloud” of sublimated (slow) film material is relatively collisionless



Results: Explosive Plasma

- Expected to generate quasi-neutral plasma near the cathode that excluded the applied field and the more mobile e^- creating charge separation that drags ions towards the anode



- Developing model for Triggered Vacuum Spark Gaps. Includes:
 - External circuit with collapsing parallel plasma resistance to get film current
 - 1D joule heating model determines surface temperature
 - e^- flux based on Murphy-Good
 - Neutral flux based on sublimation
- Not surprisingly, ion-induced SEE yield matters for breakdown
 - Desirable to have film with high SEE yield on the cathode $\rightarrow E_{iz, \text{film}} > \phi_{\text{cathode}}$
- If fast neutrals (~ 20 km/s) produced from cathode emission then significant anode electrode material can be sputtered *before* breakdown
- Future (potential) improvements:
 - Couple external circuit & material supply model to PIC-DSMC simulation
 - Better model for what happens when $T_{\text{film}} > T_{\text{boiling}}$
 - Species and velocity distribution?
 - Better cross section and ion-induced SEE data